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FACSIMILE COVER SHEET

TO: Examiner Remmon R. Forde - United States Patent and Trademark Office; Art Unit - 2826

CLIENT NAME/NUMBER: 02CT20753422

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FROM: Douglas J. Visnius

DATE: September 1, 2005

NUMBER OF PAGES (INCLUDING COVER SHEET): 12

COMMENTS/INSTRUCTIONS:

Please see attached Amendment in response to the Examiner's Office Action of June 3, 2005 for U.S. Patent Application Serial No. 10/749,134.

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Case No. 02CT20753422

MS Amendment
Commissioner For Patents
P.O. Box 1450
Alexandria, VA 22313-1450

In re Application of: **MAGRI' ET AL.**Serial No.: **10/749,134**Filed: **DECEMBER 30, 2003**For: **VERTICAL-CONDUCTION AND PLANAR-STRUCTURE MOS DEVICE WITH A DOUBLE THICKNESS OF GATE OXIDE AND METHOD REALIZING POWER VERTICAL MOS TRANSISTORS WITH IMPROVED STATIC AND DYNAMIC PERFORMANCES AND HIGH SCALING DOWN DENSITY**

Sir:

Transmitted herewith is an amendment in the above-identified application.

Applicant qualifies as a small entity under 37 CFR § 1.27.
 No additional fee is required.

The fee has been calculated as shown below:

	(Col. 1)	(Col. 2)	(Col. 3)		SMALL ENTITY			LARGE ENTITY	
FOR:	CLAIMS REMAINING AFTER AMENDMENT	HIGHEST NO. PREVIOUSLY PAID FOR	PRESENT EXTRA		RATE	Fee		RATE	Fee
TOTAL CLAIMS	35	36	0		X 25	\$	<u>OR</u>	X 50	\$ XX
INDEP. CLAIMS	4	4	0		X 100	\$	<u>OR</u>	X 200	\$ XX
<input type="checkbox"/> FIRST PRESENTATION OF MULTIPLE DEP. CLAIM				+ 180	\$	<u>OR</u>	+ 360		
					TOTAL ADD'L FEE			TOTAL ADD'L FEE	\$ 0

* If the entry in Col. 1 is less than the entry in Col. 2, write "0" in Col. 3.
 ** If the "Highest Number Previously Paid For" IN THIS SPACE is less than 20, write "20" in this space.
 *** If the "Highest Number Previously Paid For" IN THIS SPACE is less than 3, write "3" in this space. The "Highest Number Previously Paid For" (Total or Independent) is the highest number found from the equivalent box in Col. 1 of a prior amendment of the number of claims originally filed.

The Commissioner is hereby authorized to charge the fee in the amount of \$ _____ to the credit card noted in the attached credit card payment form PTO-2038.

The Commissioner is authorized to charge or credit any discrepancies in fee amounts to Deposit Account No. 01-0484.

PLEASE ADDRESS ALL CORRESPONDENCE TO ATTORNEY OF RECORD:
CHRISTOPHER F. REGAN

Please associate this application with Customer No. 27975.

September 1, 2005
 DATE



DOUGLAS J. VISNUS
 REG. NO. 48,012

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
MAGRI' ET AL.)
Serial No. 10/749,134)
Confirmation No. 3843)
Filing Date: DECEMBER 30, 2003)
For: VERTICAL-CONDUCTION AND)
PLANAR-STRUCTURE MOS DEVICE)
WITH A DOUBLE THICKNESS OF)
GATE OXIDE AND METHOD REALIZING)
POWER VERTICAL MOS TRANSISTORS)
WITH IMPROVED STATIC AND)
DYNAMIC PERFORMANCES AND HIGH)
SCALING DOWN DENSITY)
)

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Examiner: R. FORDE
Art Unit: 2826AMENDMENT

MS Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Responsive to the Official Action of June 3, 2005,
please enter the amendments and remarks set out below.